

KU PA 080090-08 A, GaAs-FET Power Amplifier 800 ... 900 MHz



Features

- High linearity
- Reverse polarity protection
- Milled aluminium case
- Small mechanical dimensions

Applications

- Low power applications
- Driver amplifier
- Analog and digital transmission systems

Important notes

Please notice the following:

- The technical specifications refer to room temperature.
- The power amplifier doesn't contain any coaxial relays.
- The recommended combination of heat sink and fan(s) is only specified for an ambient temperature of 25 °C.
- Further information about dimensioning of heat sinks is available on our FAQ site.

Technical specifications:

Frequency range	800..900 MHz
Input power for P1dB	min. 14 dBm
Maximum input power	+17 dBm
Output power P1dB	typ. 29 dBm (CW) typ. 800 mW (CW)
Output power P3dB	typ. 30 dBm (CW) typ. 1 W (CW)
Output power COFDM (1)	min. 23 dBm min. 200 mW
Gain (small signal)	min. 15 dB
Gain flatness (small signal)	+/-0.5 dB (typ.)
Harmonic rejection	min. 28 dB @ 28.7 dBm
IM3 (2)	min. 46 dBc @ 24.7 dBm PEP
Efficiency	min. 20 % @ 29 dBm (CW)
Supply voltage	+12 ... 14 V DC
Quiescent current	typ. 0.35 A
Current consumption	typ. 0.35 A
Operating case temp. range	-20 ... +55 °C
VSWR of load	max. 1.8 : 1
Input connector / impedance	N-female / 50 ohms
Output connector / impedance	N-female / 50 Ohms
Case	milled aluminium
Dimensions (mm)	50 x 30 x 22
Weight	90 g (typ.)

(1)	Measured with QAM 64, single carrier, EVM: 2%
(2)	Measured 2-tone, frequency spacing: 1 MHz